# 2SD2420, 2SD2420A

## Silicon NPN triple diffusion planar type darlington

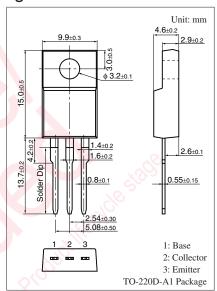
For power amplification
Complementary to 2SB1623, 2SB1623A

#### ■ Features

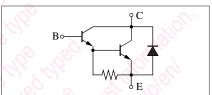
- High forward current transfer ratio h<sub>FE</sub>
- Dielectric breakdown voltage of the package: > 5 kV

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SD2420	V <sub>CBO</sub>	60	V
(Emitter open)	2SD2420A		80	
Collector-emitter voltage	2SD2420	V <sub>CEO</sub>	60	V
(Base open)	2SD2420A		80	
Emitter-base voltage (Col	$V_{EBO}$	5	V	
Collector current	$I_{C}$	4	A	
Peak collector current	$I_{CP}$	8	A	
Collector power		$P_{C}$	30	W
dissipation	$T_a = 25^{\circ}C$		2.0	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



#### Internal Connection



### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	$I_C = 30 \text{ mA}, I_B = 0$	60			V
Base-emitter voltage		$V_{BE}$	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$	70	5	2.5	V
Collector-base cutoff	2SD2420	$I_{CBO}$	$V_{CB} = 60 \text{ V}, I_{E} = 0$	0/1		200	μΑ
current (Emitter open)	2SD2420A	,	$V_{CB} = 80 \text{ V}, I_{E} = 0$	7.7		200	
Collector-emitter cutoff	2SD2420	$I_{CEO}$	$V_{CE} = 30 \text{ V}, I_{B} = 0$	7		500	μΑ
current (Base open)	2SD2420A		$V_{CE} = 40 \text{ V}, I_{B} = 0$			500	
Emitter-base cutoff current (Colle	ector open)	$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_{C} = 0$			2	mA
Forward current transfer ratio		h <sub>FE1</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 0.5 \text{ A}$	1 000			_
		h <sub>FE2</sub> *	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$	2000		10 000	
Collector-emitter saturation v	oltage	V <sub>CE(sat)1</sub>	$I_C = 3 \text{ A}, I_B = 12 \text{ mA}$			2.0	V
		V <sub>CE(sat)2</sub>	$I_C = 5 \text{ A}, I_B = 20 \text{ mA}$			4.0	
Transition frequency		$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t <sub>on</sub>	$I_C = 3 \text{ A}, I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA}$		0.5		μs
Storage time		t <sub>stg</sub>	$V_{CC} = 50 \text{ V}$		4.0		μs
Fall time		$t_{\mathrm{f}}$			1.0		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*: Rank classification

Rank	Q	Р		
h <sub>FE2</sub>	2000 to 5000	4000 to 10000		

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